

SILICON NPN TRIPLE DIFFUSED TYPE
(DARLINGTON POWER)

2SD683
2SD683A

HIGH VOLTAGE AND HIGH POWER SWITCHING APPLICATIONS.
MOTOR DRIVE APPLICATIONS.

INDUSTRIAL APPLICATIONS

Unit in mm

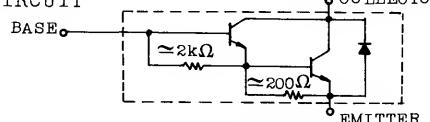
FEATURES :

- High DC Current Gain : $hFE=500$ (Min.) ($V_{CE}=5V$, $I_C=5A$)
- High Voltage : $V_{CEO}(SUS)=450V$ (2SD683A)
- Monolithic Construction With Built-In Base-Emitter Shunt Resistor.

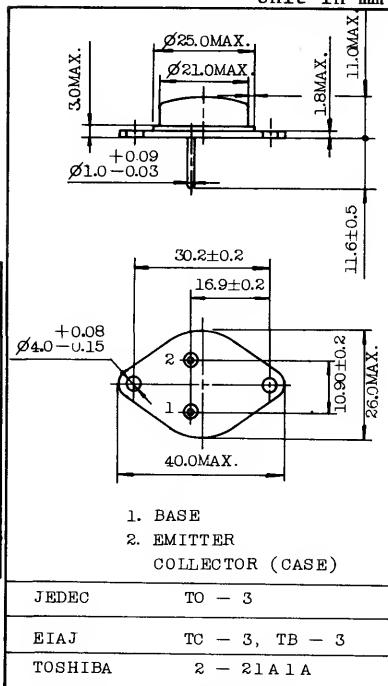
MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage	V_{CEO}	400	V
		450	
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	15	A
Base Current	I_B	2	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	150	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65~150	$^\circ C$

EQUIVALENT CIRCUIT



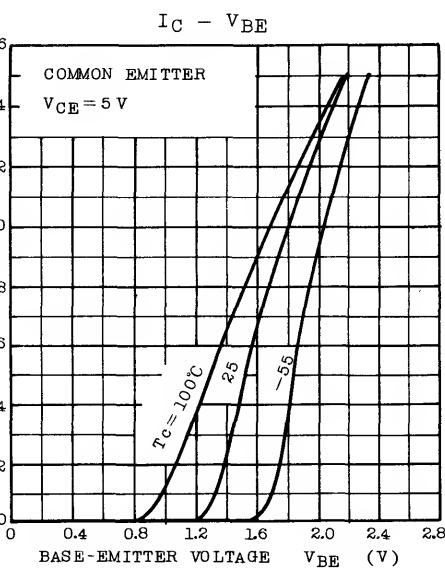
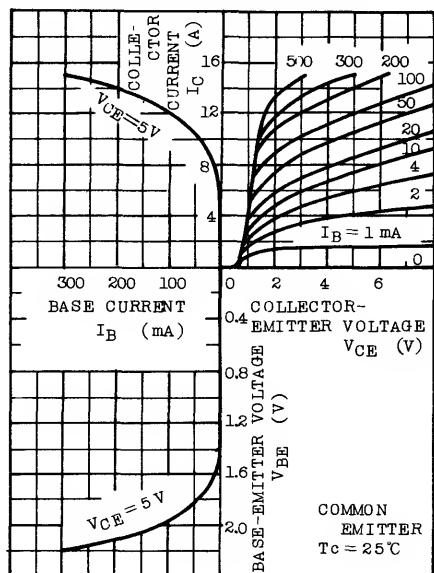
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)



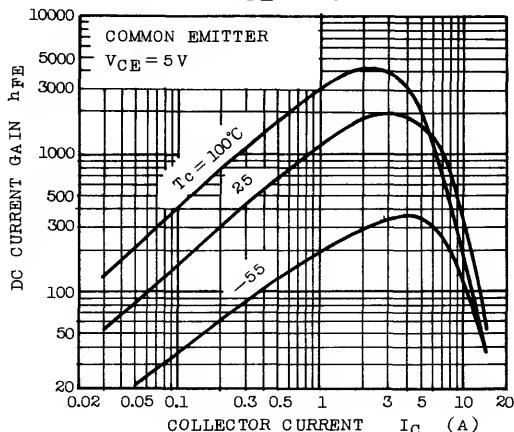
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=600V$, $I_E=0$	-	-	0.5	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V$, $I_C=0$	-	-	30	mA
Collector-Emitter Sustaining Voltage	$V_{CEO}(SUS)$	$I_C=5A$, $L=10mH$	400	-	-	V
			450	-	-	
DC Current Gain	$h_{FE}(1)$	$V_{CE}=5V$, $I_C=5A$	500	-	-	
	$h_{FE}(2)$	$V_{CE}=5V$, $I_C=15A$	30	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A$, $I_B=0.2A$	-	-	2.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10A$, $I_B=0.2A$	-	-	2.5	V
Emitter-Collector Forward Voltage	V_{ECF}	$I_E=10A$, $I_B=0$	-	-	3.0	V
Collector Output Capacitance	C_{ob}	$V_{CB}=50V$, $I_E=0$, $f=1MHz$	-	100	-	pF
Switching Time	Turn-on Time	t_{on}	20μs	I_{B1}	I_{B2}	μs
	Storage Time	t_{stg}		I_{B1}	I_{B2}	
	Fall Time	t_f		$I_{B1} = -I_{B2} = 0.1A$	DUTY CYCLE $\leq 1\%$	

2SD683•2SD683A

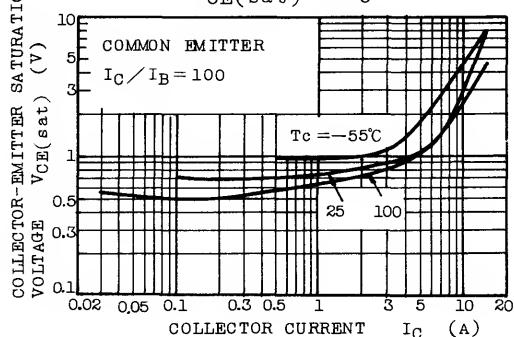
STATIC CHARACTERISTICS



$h_{FE} - I_C$



$V_{CE(\text{sat})} - I_C$



$V_{BE(\text{sat})} - I_C$

